L Number	Hits	Search Text	DB	Time stamp
1	7369	(((((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad wafer))) and (silicon near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 16:23
2	1793	((((((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad wafer))) and (silicon near layer)) and ((refractory near metal) (titanium near tungsten) (titanium near nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 16:25

L Number	Hits	Search Text	DB	Time stamp
49	220768	((silicon near on insulator) (SOI))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 13:22
50	25450	(((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 13:23
51	12751	((((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 13:24
53	7369	(((((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad wafer))) and (silicon near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 13:32
54	904	((((((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad wafer))) and (silicon near layer)) and (refractory near metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 13:33